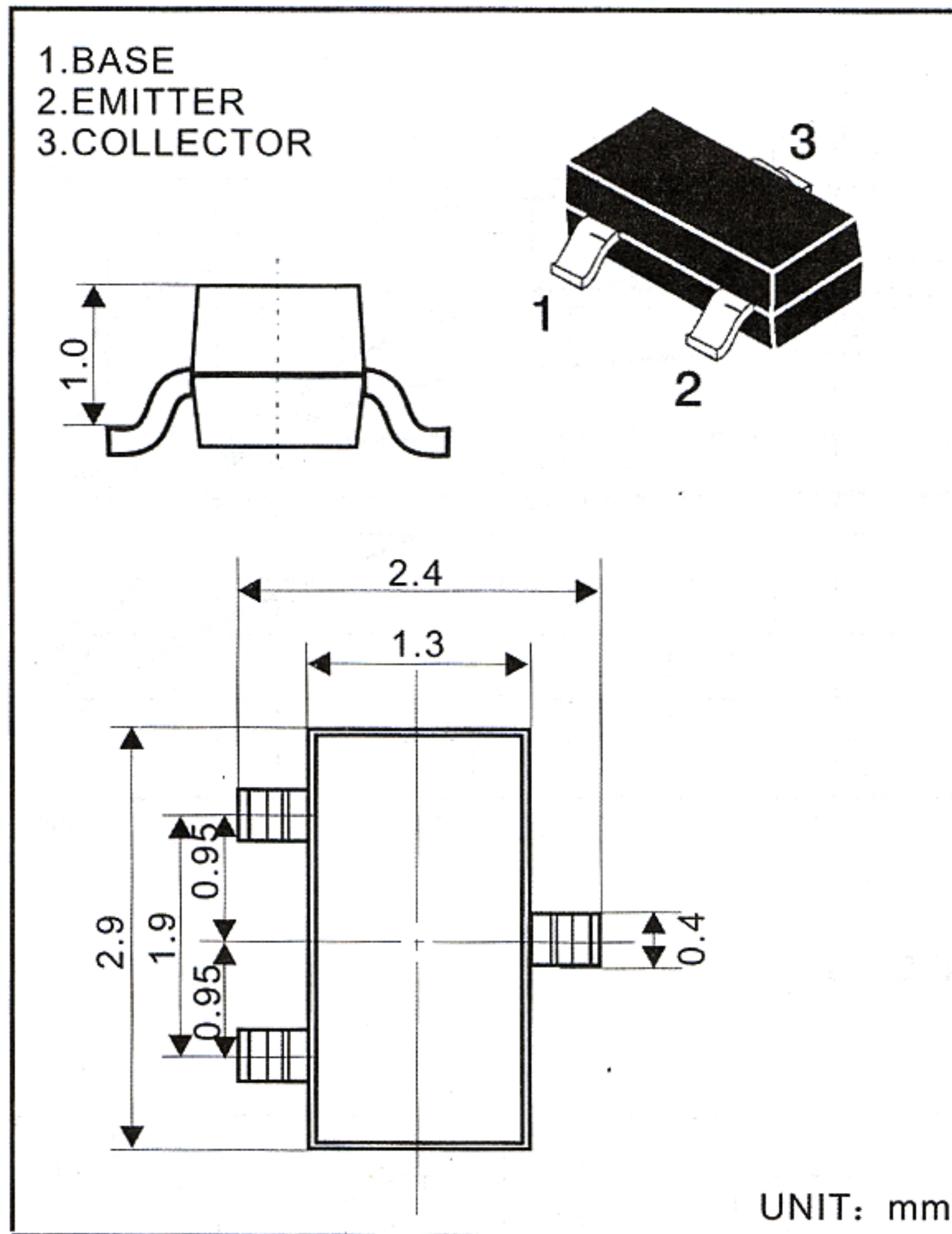


MMBT4401LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM} : 0.225 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 60V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

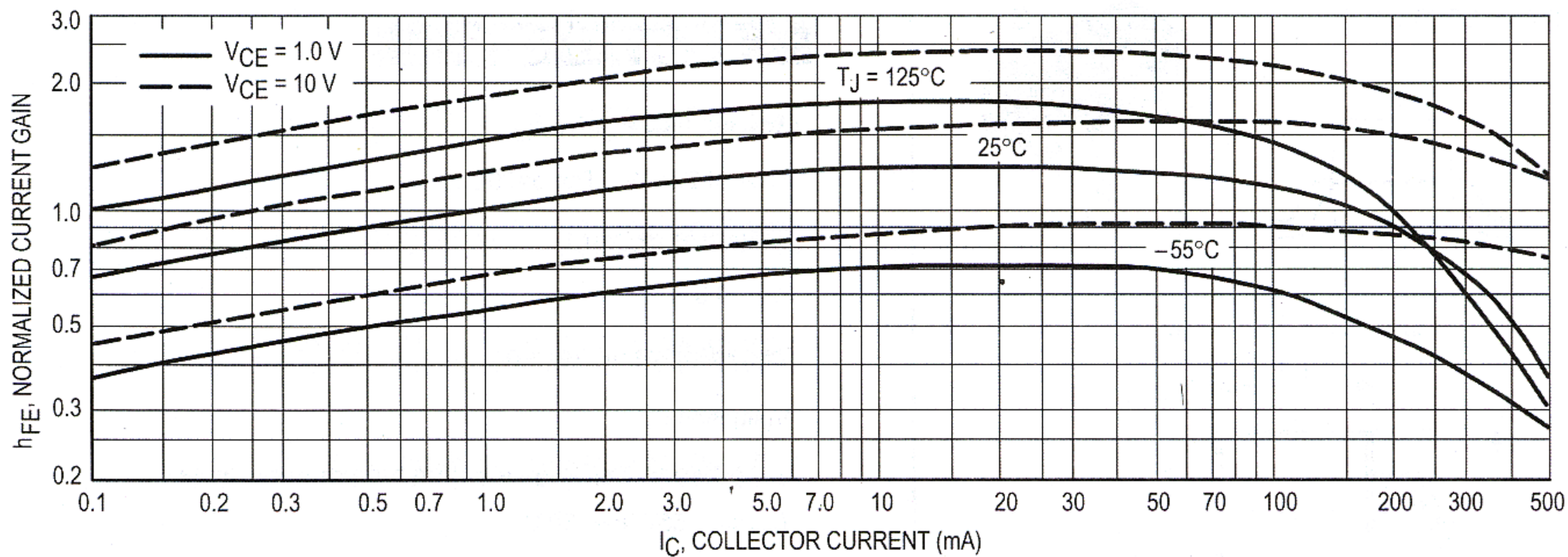
ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

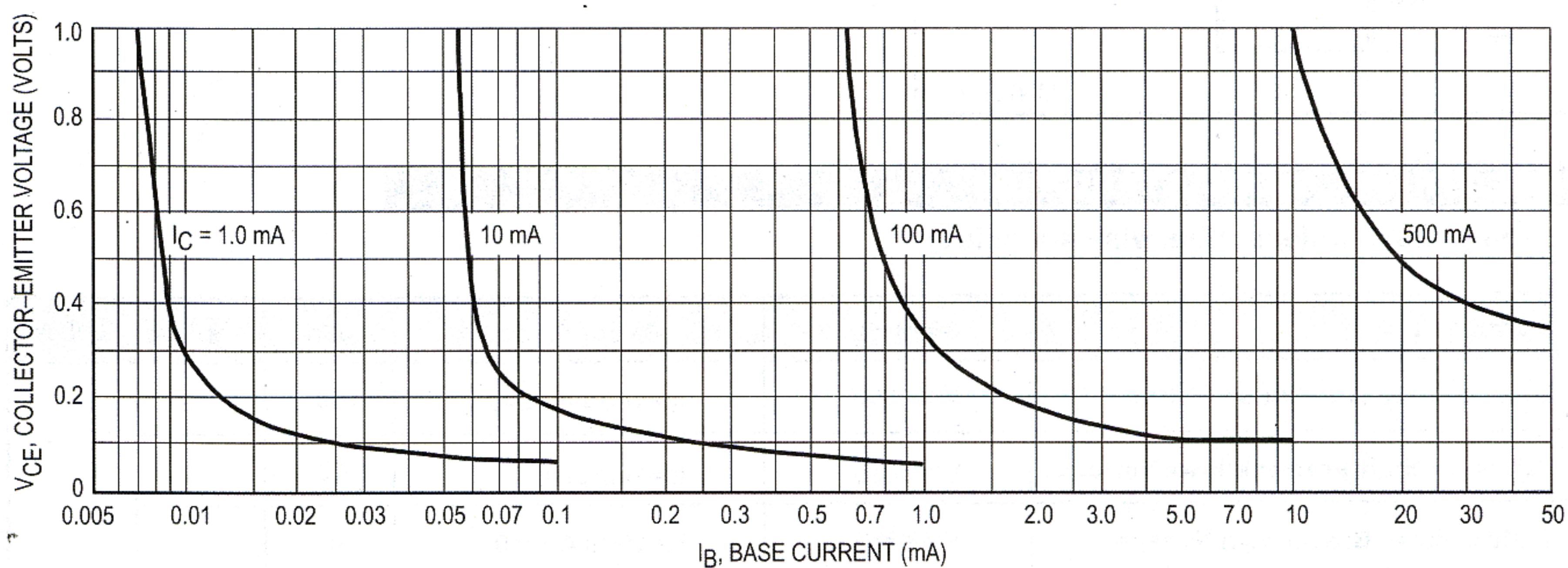
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Drain-source Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6		
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V, I_E=0$		0.1	μA
	I_{CEO}	$V_{CE}=35V, I_B=0$		0.1	
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=150mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=500mA$	40		
Collector-emitter Saturation Voltage	V_{CEsat}	$I_C=150mA, I_B=15mA$		0.4	V
Base-emitter Voltage	V_{BEsat}	$I_C=150mA, I_B=15mA$		0.95	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=20mA$ $f=100MHz$	250		MHz

Typical Characteristics

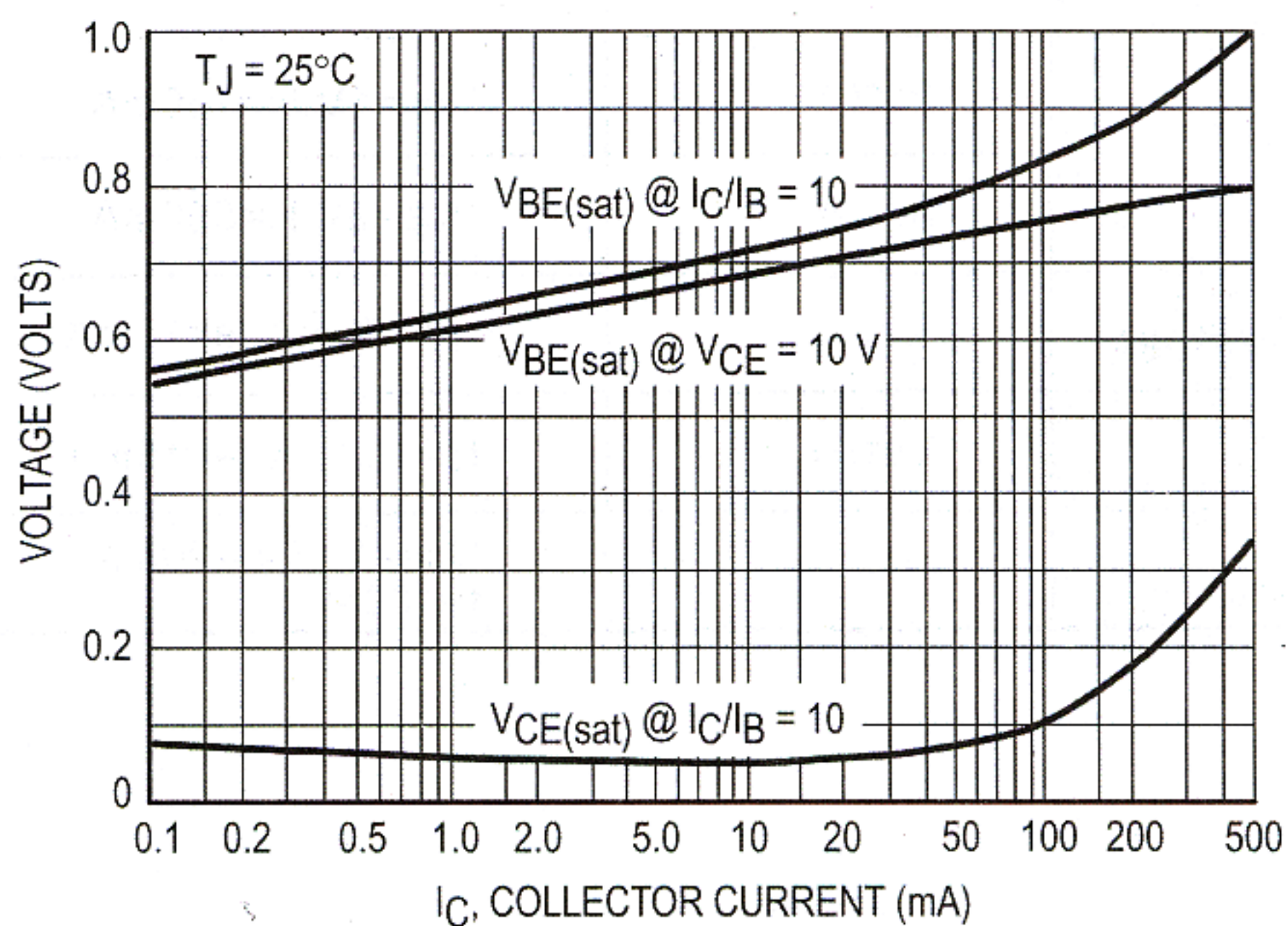
MMBT4401LT1



DC Current Gain



Collector Saturation Region



"On" Voltages